## UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

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**APPLICATION NO. : 09/661766** 

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INVENTOR(S)

: Gormley et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In Column 10, claim 10, line 64, delete "second stop layer being bonded to the one of the second and" and replace with --second etch stop layer being bonded to the one of the second and ---

In Column 11, claim 17, line 18, delete "16" and replace with --15--

In Column 11, claim 20, line 30, delete "second and third layers and of semiconductor material." and replace with -- second and third layers are of semiconductor material.--

In Column 12, claim 31, line 23, delete the word "each" and insert the word --etch-

In Column 12, claim 38, line 48, delete "first layer is at least half the area of the component in plan" and insert --first layer adjacent the component is at least half the area of the component in plan--

Signed and Sealed this

Seventeenth Day of April, 2007

JON W. DUDAS Director of the United States Patent and Trademark Office